

Bimodal growth mode of Fe/cc(110) ; cc=(W,Mo)

Application to the self-organization of thick stripes



O.Fruchart,

Laboratoire Louis Néel (CNRS), Grenoble



- **Evidence for bimodal growth**
- **Application to self-organized thick stripes**
- **Extend versatility of self-assembly**
- **Discussion of results from the literature**



Growth processes

- **Motivation**: model system for 2D magnetism (no alloying, pseudomorphic, layer-by-layer)
- **Growth**:
 - Pseudomorphic 1st layer, then Stranski-Krastanov
 - Kinetic roughness along [001] at room temperature
 - Progressive increase of temperature for flat films
 - Dots at high temperature
- **Substrate**: qualitatively (if not quantitatively) similar results for W(110) and Mo(110).

Self-organization

- Step-decoration of vicinal surfaces: 0.5ML, 1.5ML.
Curie temperature < 300K

Key references

- **Pioneering**: Gradmann82, Tikhov-Bauer90
- **Following**: Elmers-Gradmann90, Albrecht-Gradmann93, Bethge95
- **Stripes**: Hauschild-Gradmann98, Bode-Wiesendanger00



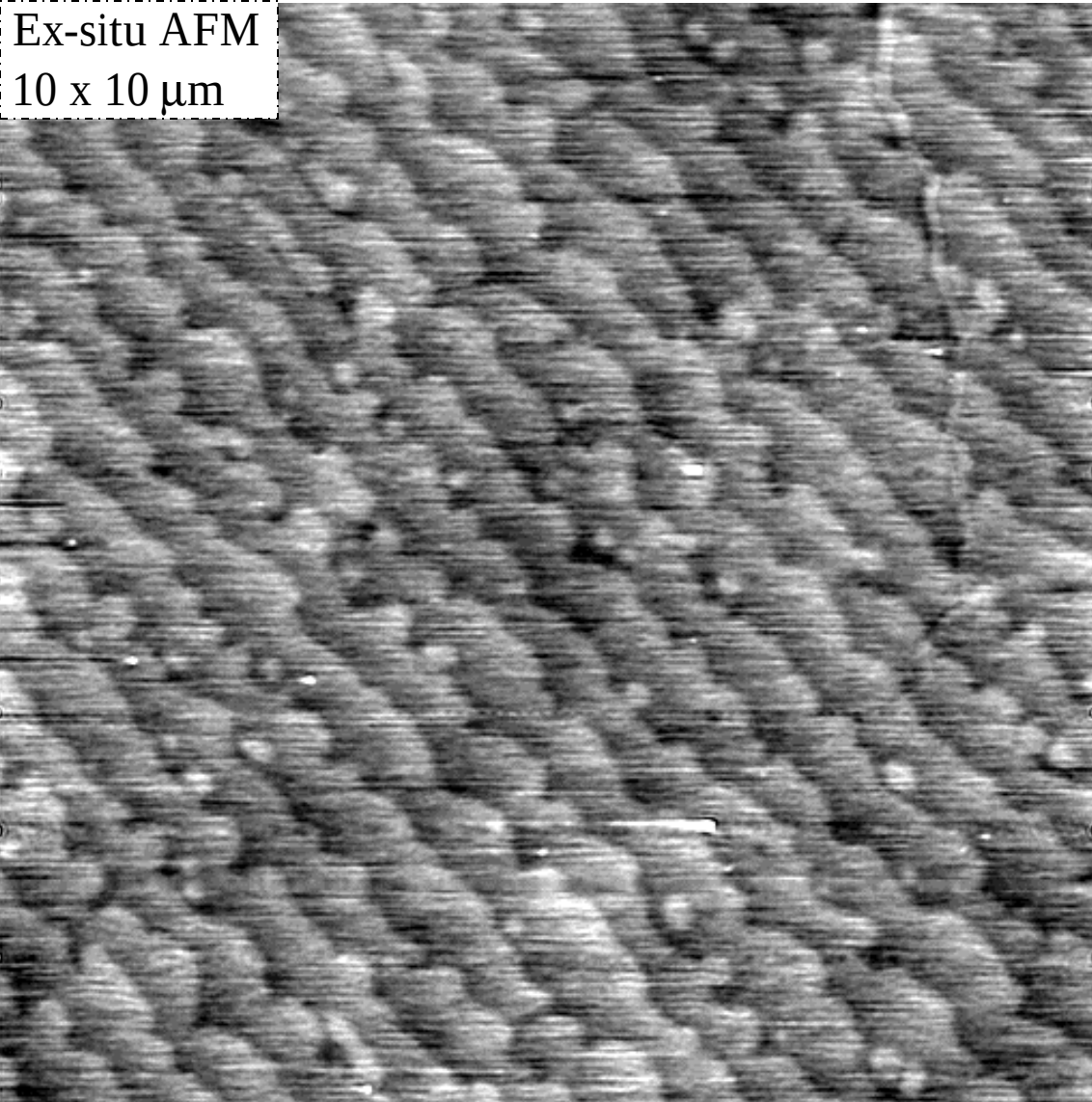
PULSED LASER DEPOSITION,

Nd:YAG
Pulsed Laser

Target

cc(110)/Al₂O₃
cc=Mo, W,

Ex-situ AFM
10 x 10 μm



cc(110) s

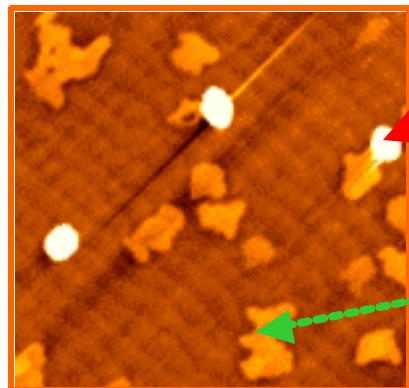
Mo[001]



Buffer layer growth : O. Fruchart, S. Jaren, J. Rothman, *Appl. Surf. Sci.* **135**, 218 (1998)

MBE versus PLD : J. .Shen et al., *Surf. Sci. Rep.*, **52**, 163 (2004) Olivier Fruchart – ICCG14 – Aug. 2004 – p.6

$e_{\text{nom}} = 0.7 \text{ nm} \sim 3.5\text{ML}$

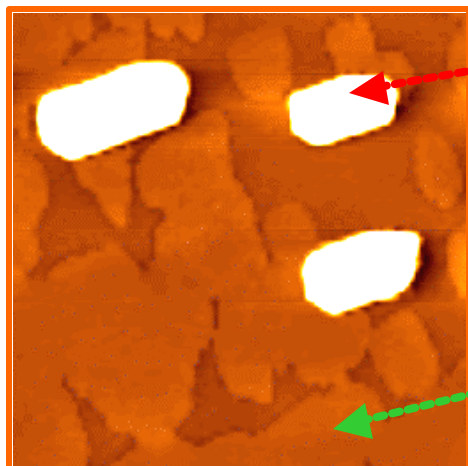


50% Vol. 3D

$h=1.2\text{nm}$
50% Vol. Flat

AFM, $3\mu\text{m} \times 2.8\mu\text{m}$

$e_{\text{nom}} = 8 \text{ nm} \sim 40\text{ML}$



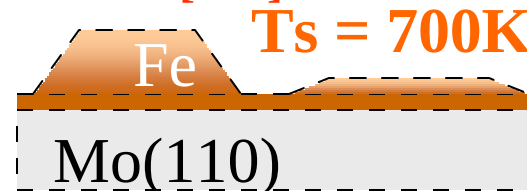
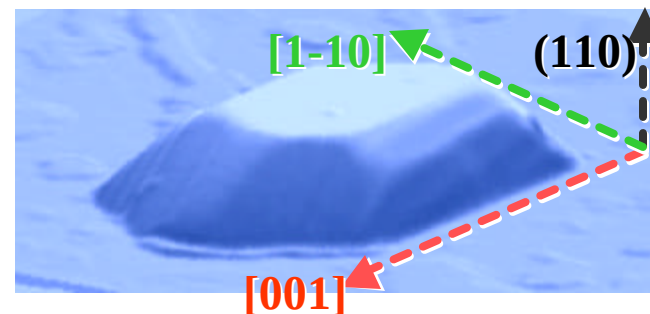
90% Vol. 3D

$h=1.2\text{nm}$
10% Vol. Flat

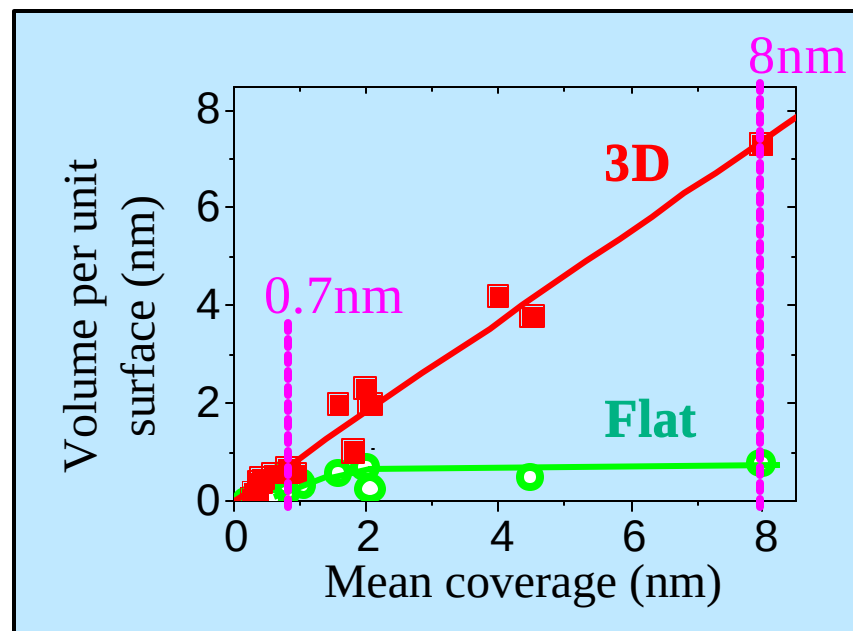
AFM, $3.6\mu\text{m} \times 3.6\mu\text{m}$

P.-O.Jubert *et al.*, JMMM 226, 1842 (2001)

P.-O.Jubert *et al.*, PRB64, 115419 (2002)



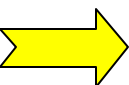
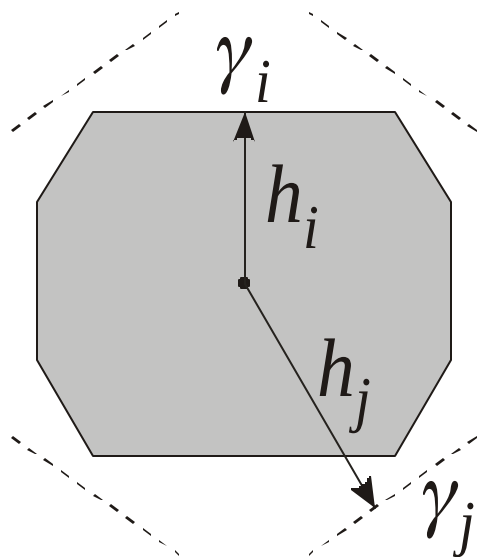
Bimodal Stranski-Krastanov growth



Wulff's theorem

Free crystal

$$\frac{\gamma_i}{h_i} = \text{Constant}$$

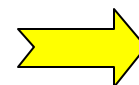
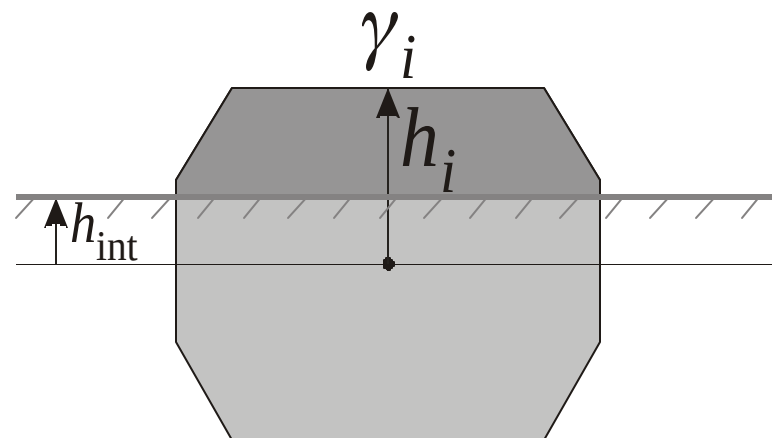


No facets with high surface energy

Wulff Kaishev's theorem

Supported crystal (growth on surfaces)

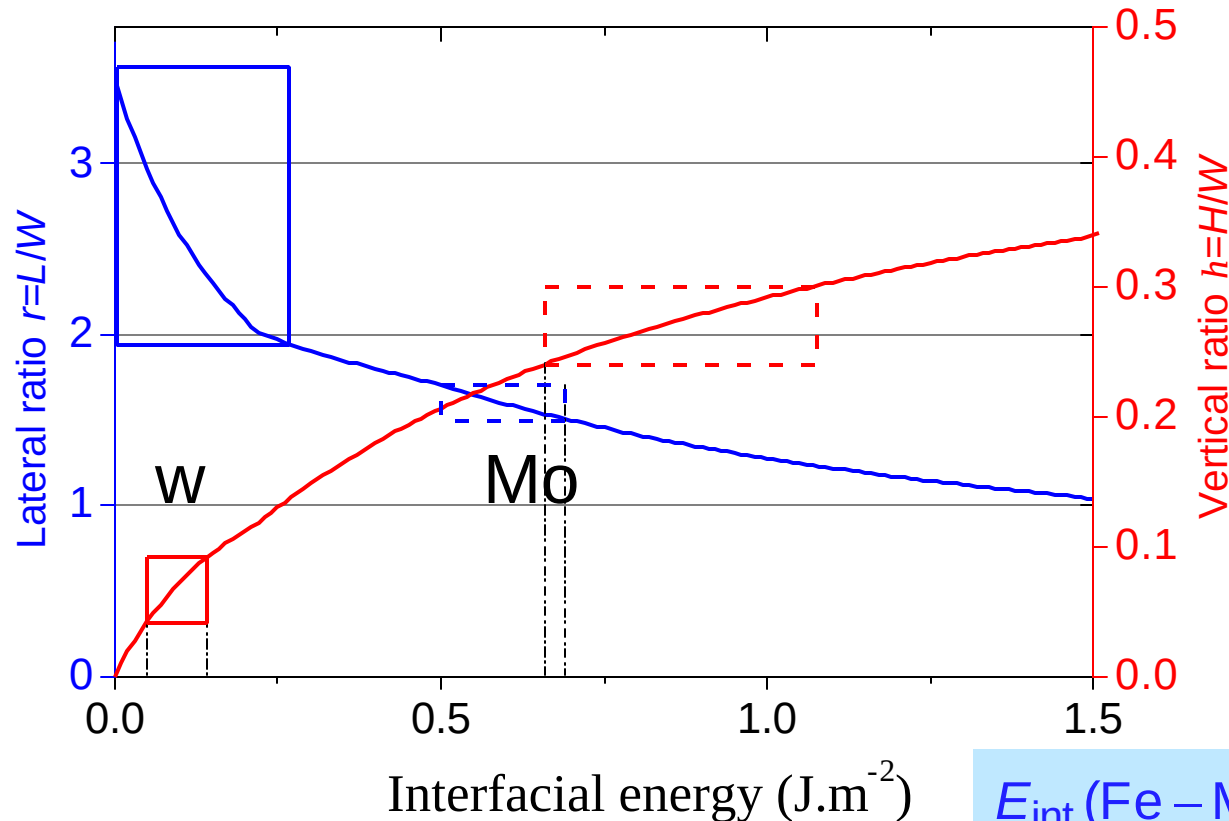
$$\frac{\gamma_i}{h_i} = \frac{\gamma_S - \gamma_{\text{int}}}{h_{\text{int}}} = \text{Constant}$$



Truncated crystal

Interface energy deduced from measurements

Based on Wulff's construction



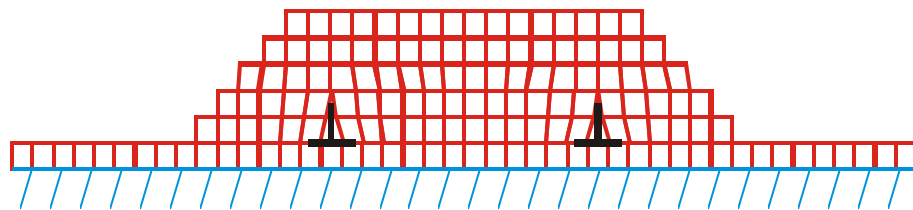
$$E_{\text{int}}(\text{Fe} - \text{Mo}) = 0.65 \pm 0.15 \text{ J.m}^{-2}$$

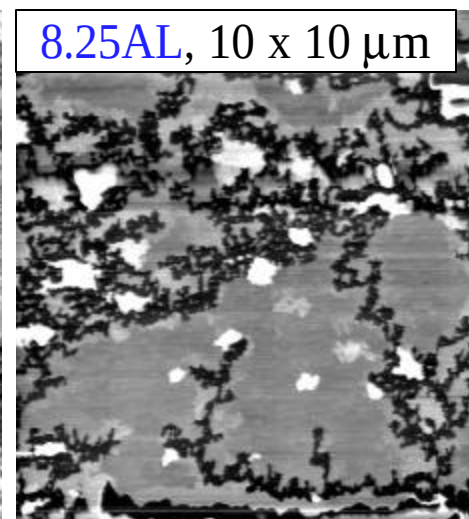
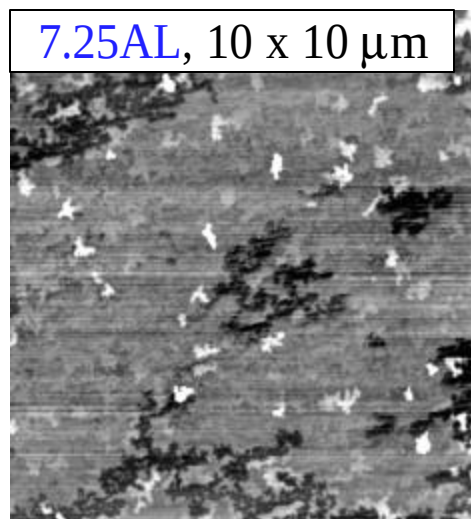
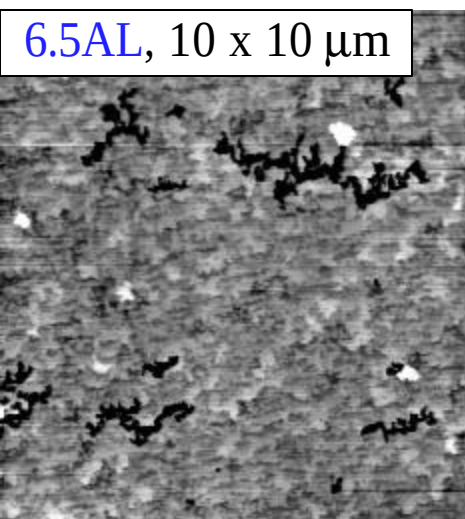
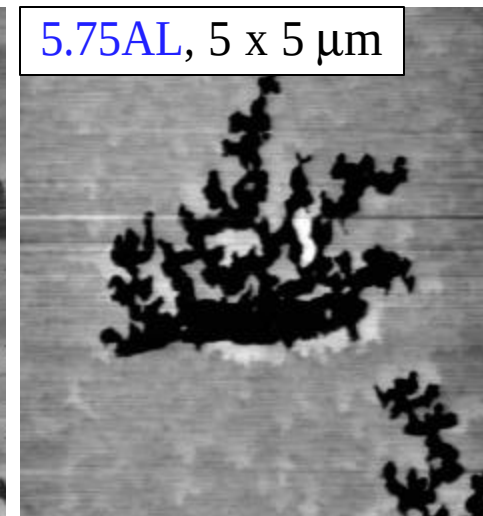
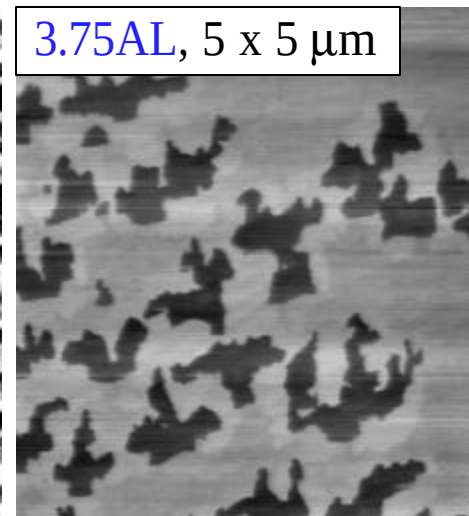
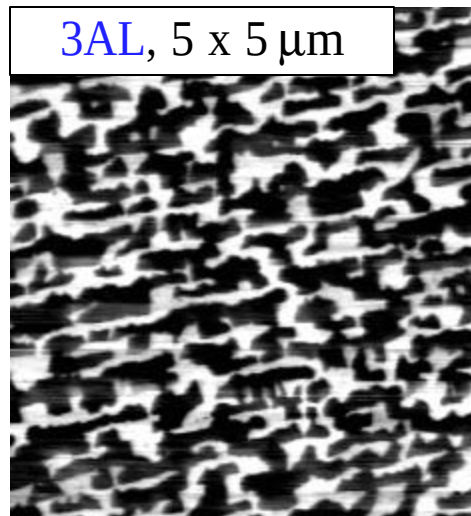
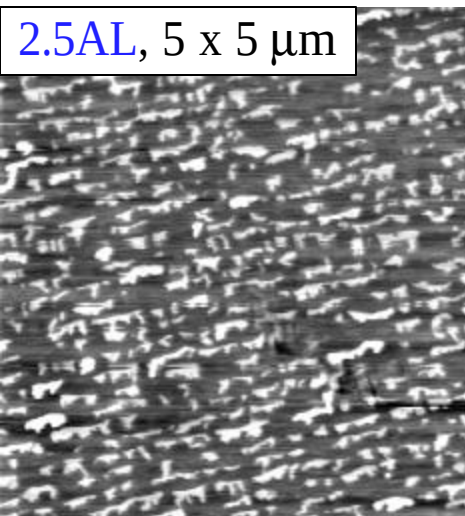
$$E_{\text{int}}(\text{Fe} - \text{W}) = 0.15 \pm 0.1 \text{ J.m}^{-2}$$

Micron-size dots:

Includes interfacial dislocation energy

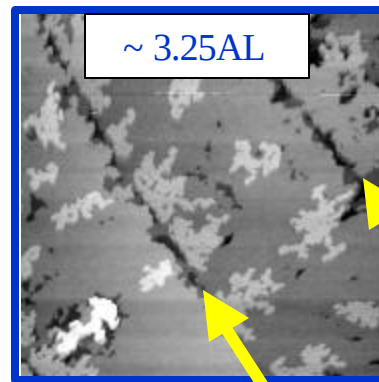
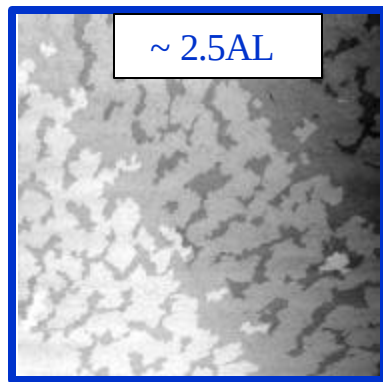
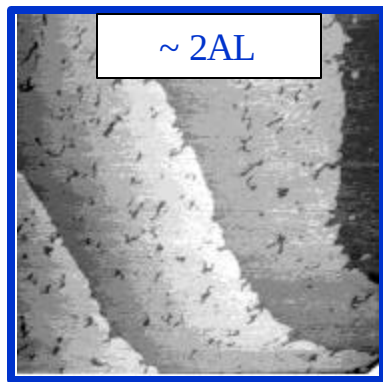
↪ Effective interface energy



**25°C growth + 450°C Annealing - Ex-situ AFM**

- **t < 7AL:**
7AL metastable patches
- **t > 7AL:**
patches are 'sucked'
- ↪ 3D dots more stable than 7AL patches.

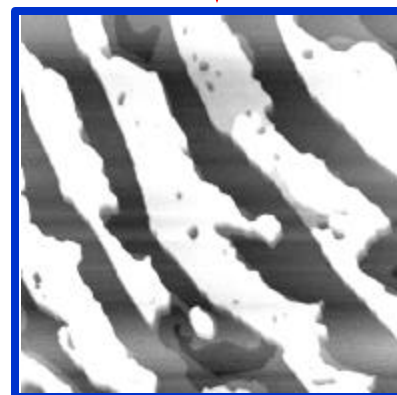
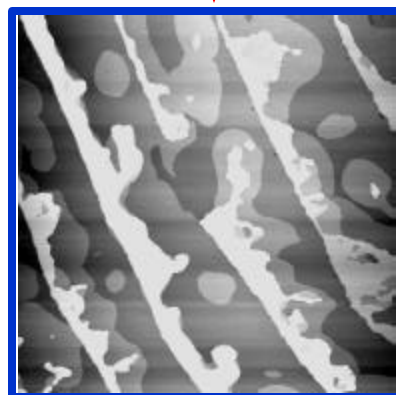
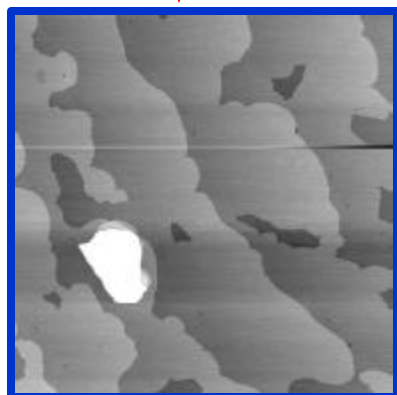
Step 1: layer-by-layer growth at 150°C



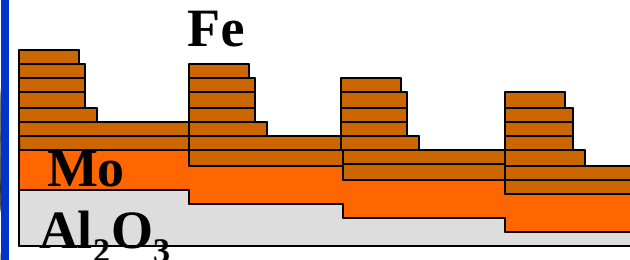
Fe films grown at 150°C

STM, 600nm x 600nm

Step 2: annealing at 500°C --> stripes along steps

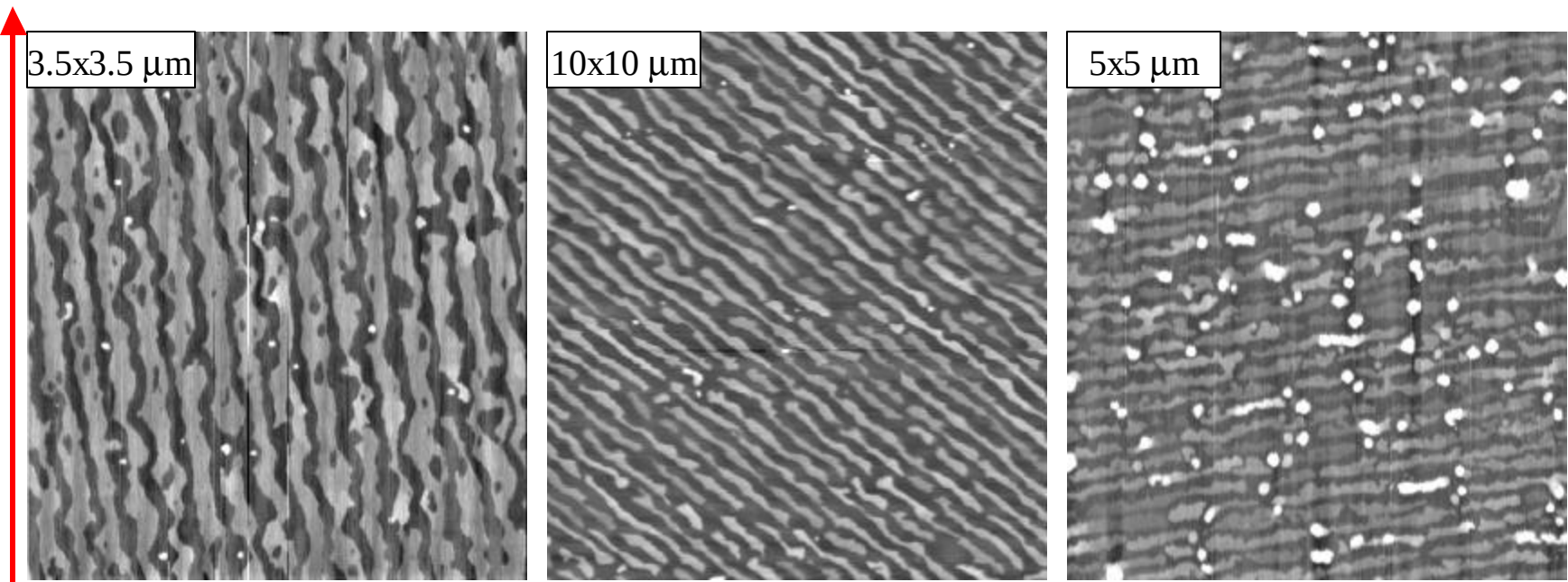


STM, 750nm x 750nm





Fe[001]



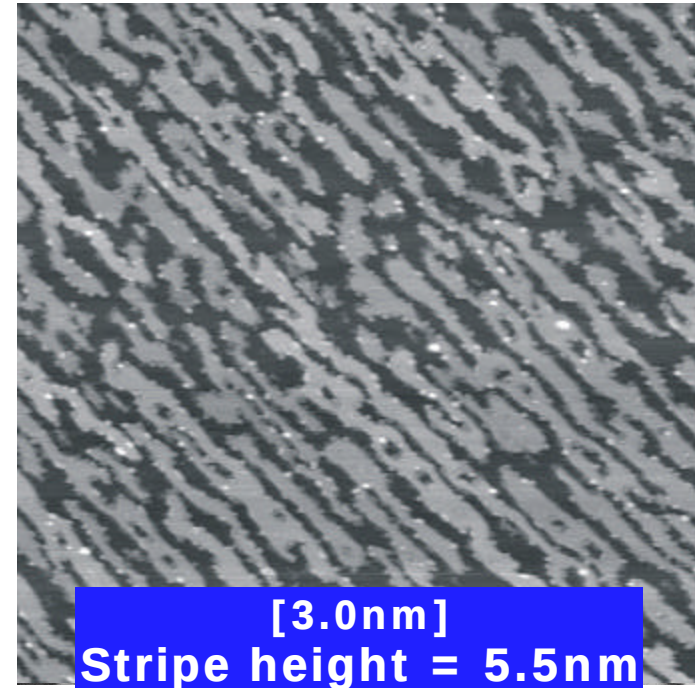
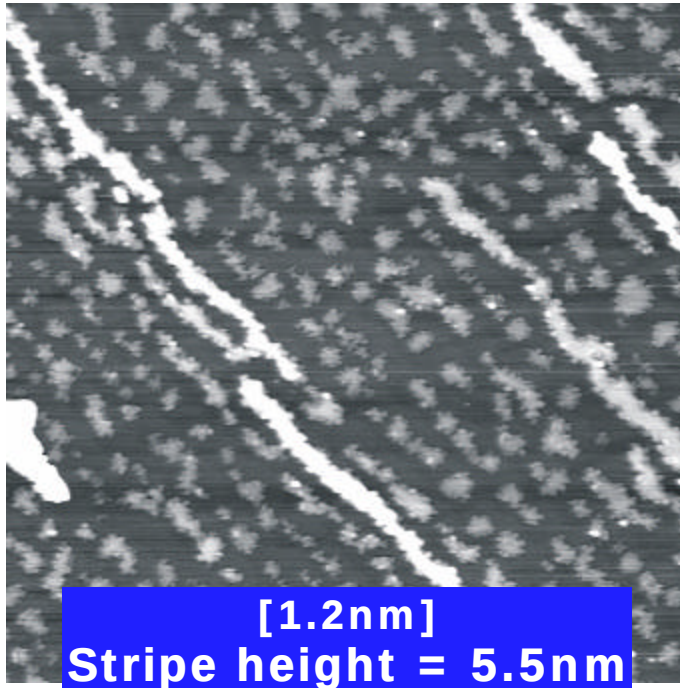
Fe[1-10]

(Slightly too high temperature
for this sample...)

- ↪ 7ML stripes (instead of 1-2ML usually)
- ↪ Tunable orientation
- ↪ To be optimized for better quality



Sapphire\W(8nm)\Fe(150°C + 450°C annealing)



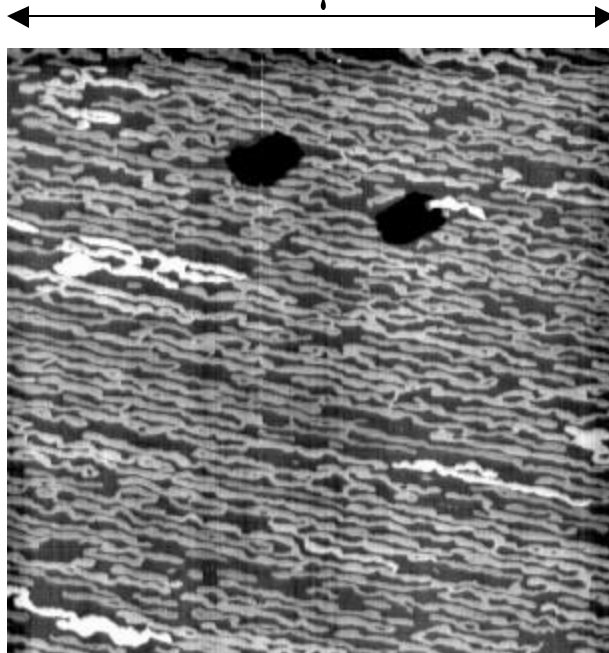
- ↪ Stripes for Fe/W(110)
- ↪ Increased height : 5.5nm
(significant advancement compared with existing literature)



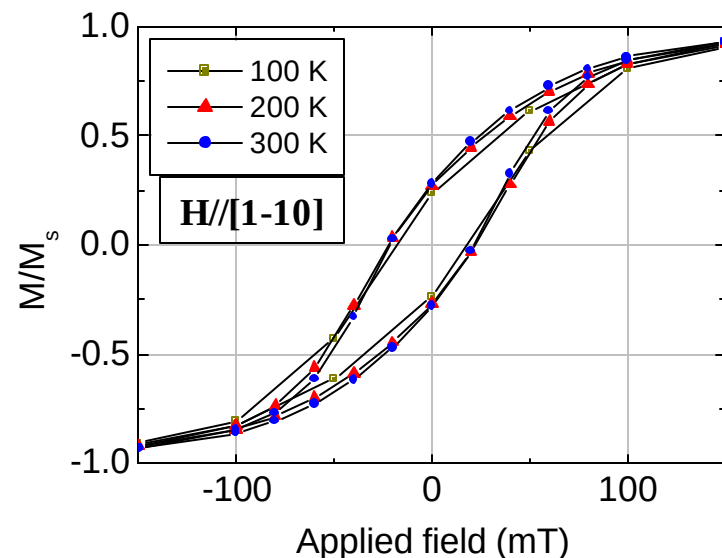
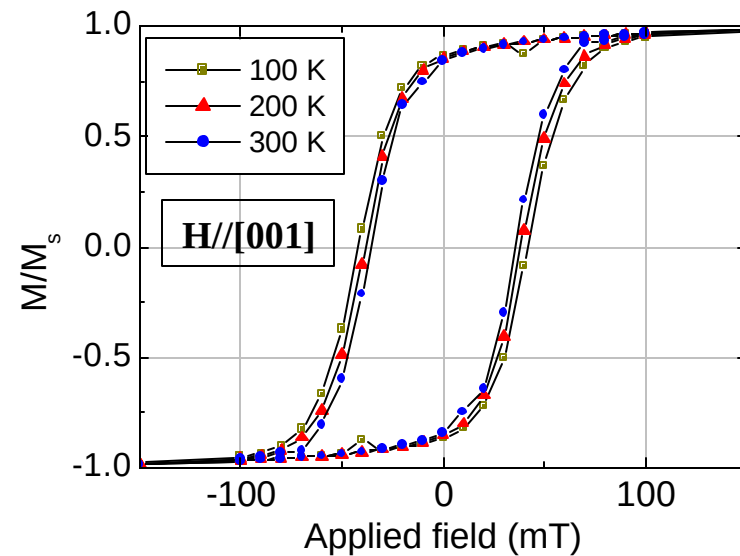
Coercivity and remanence at 300K

Sapphire \ W \ Fe(3nm) \ Mo

10 μm



- ↗ Coercivity and high remanence at 300K
- ↗ Weak temperature dependence
- > **behaves like a conventional material**

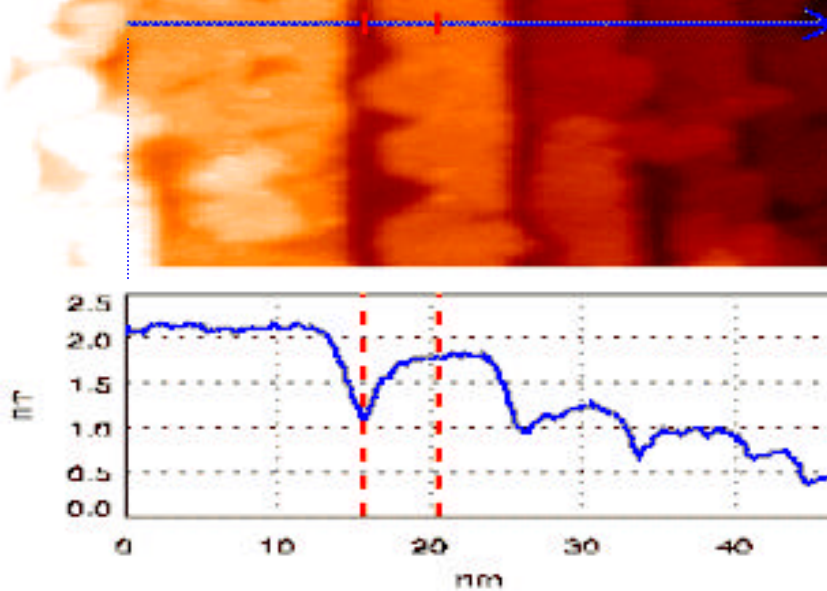


STM, 80x70 nm

3 ML $\text{Fe}_{65}\text{Ni}_{35}$ /
Cu(111)-vic 1.2°

↪ Grooves along steps

General phenomenon
that may be exploited ?



S. Cherifi *et al.*, PRB 64 (2001) 184405



Quantum confinement

Evidence for 'magic' heights have been reported for several systems:

Pb/Cu(111): 6,8,11,15,17,20 ML. **R. Otero et al., PRB66, 115401 (2002)**

Ag/GaAs: A.R. Smith et al., **Science 273, 226 (1996)**

Ag/Si(111): L. Gavioli et al., **Phys. Rev. Lett. 82, 129 (1999)**
L. Huang et al., Surf. Sci. 416, L1101 (1998)

Pb/Si(111): **V. Yeh et al., Phys. Rev. Lett. 85, 5158 (2000)**
W. B. Su et al., Phys. Rev. Lett. 86, 5116 (2001)

Au/Fe(001): 5ML, **D. A. Luh et al., Science 292, 1131 (2001)**

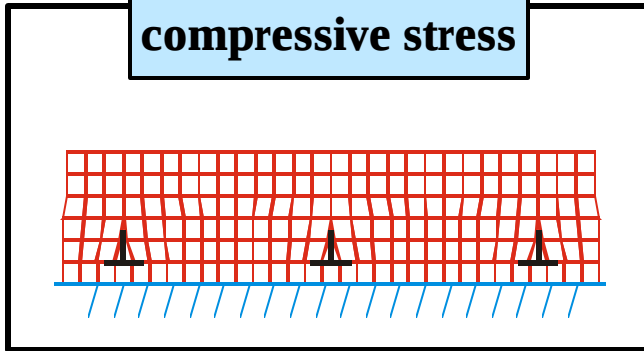
However, several magical heights would be expected...



Under investigation

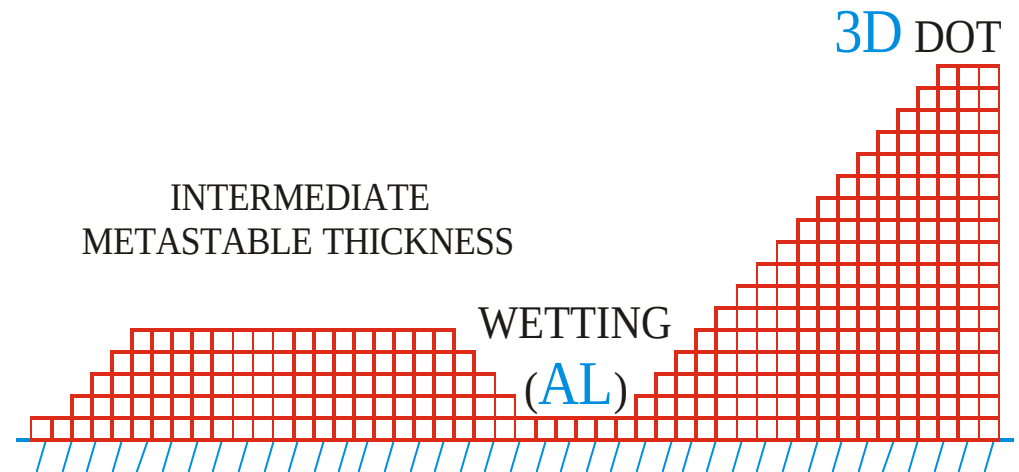
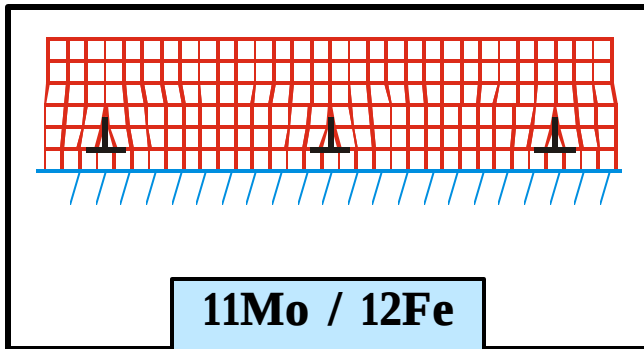
Transition of the interfacial dislocation network

**10Mo / 11Fe
compressive stress**



**Possible explanation = elastic energy minimization
commensurate / incommensurate transition of
interface dislocation array at the 'magical'
thickness.**

**11Mo / 12Fe
tensile stress**

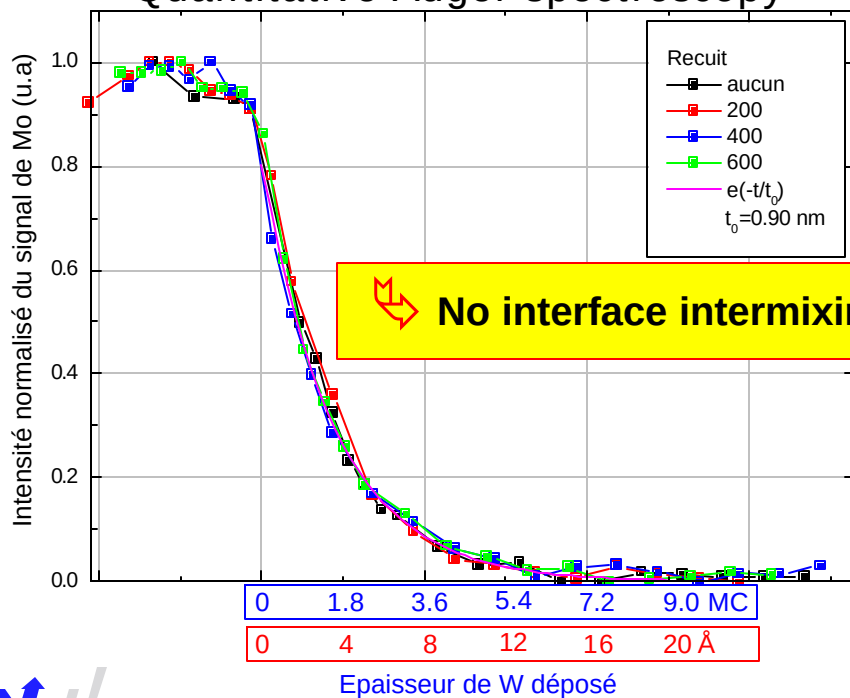


Control interface independently from lattice parameter

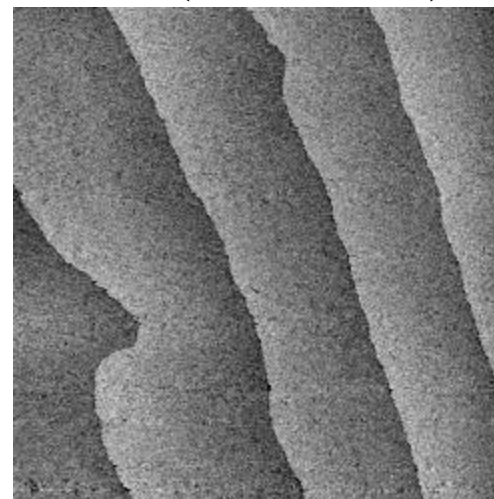


25°C growth
+ 800°C Annealing

Quantitative Auger spectroscopy



STM (800x800 nm)



Atomically-flat surface

Continuous control of lattice parameter

Opposite wedges

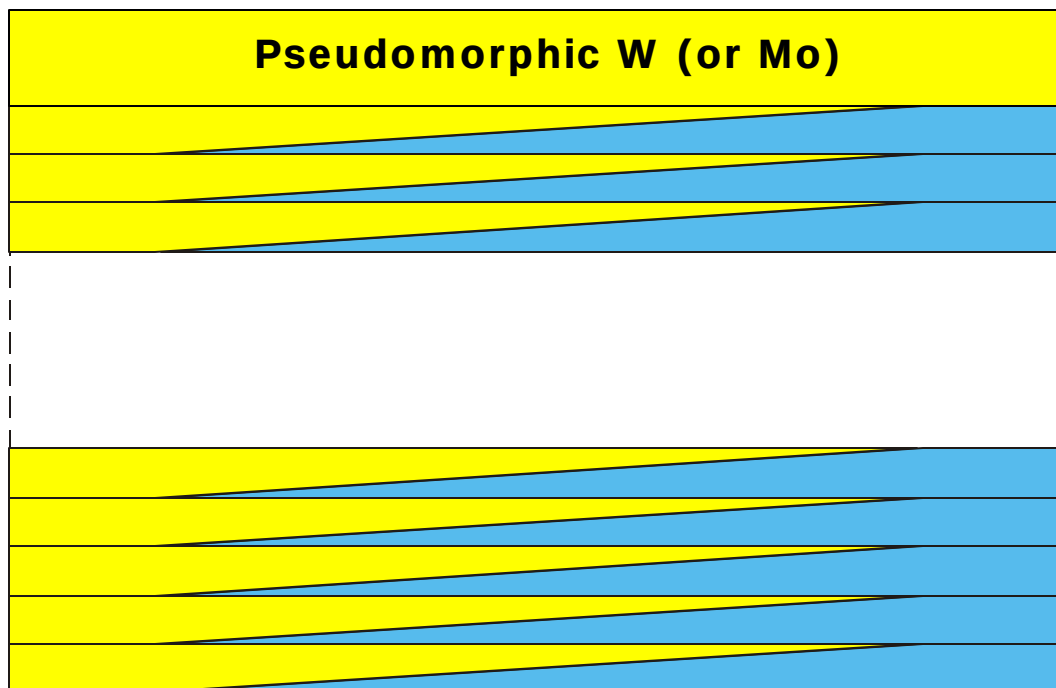
3.165 Å

W

'mixture'

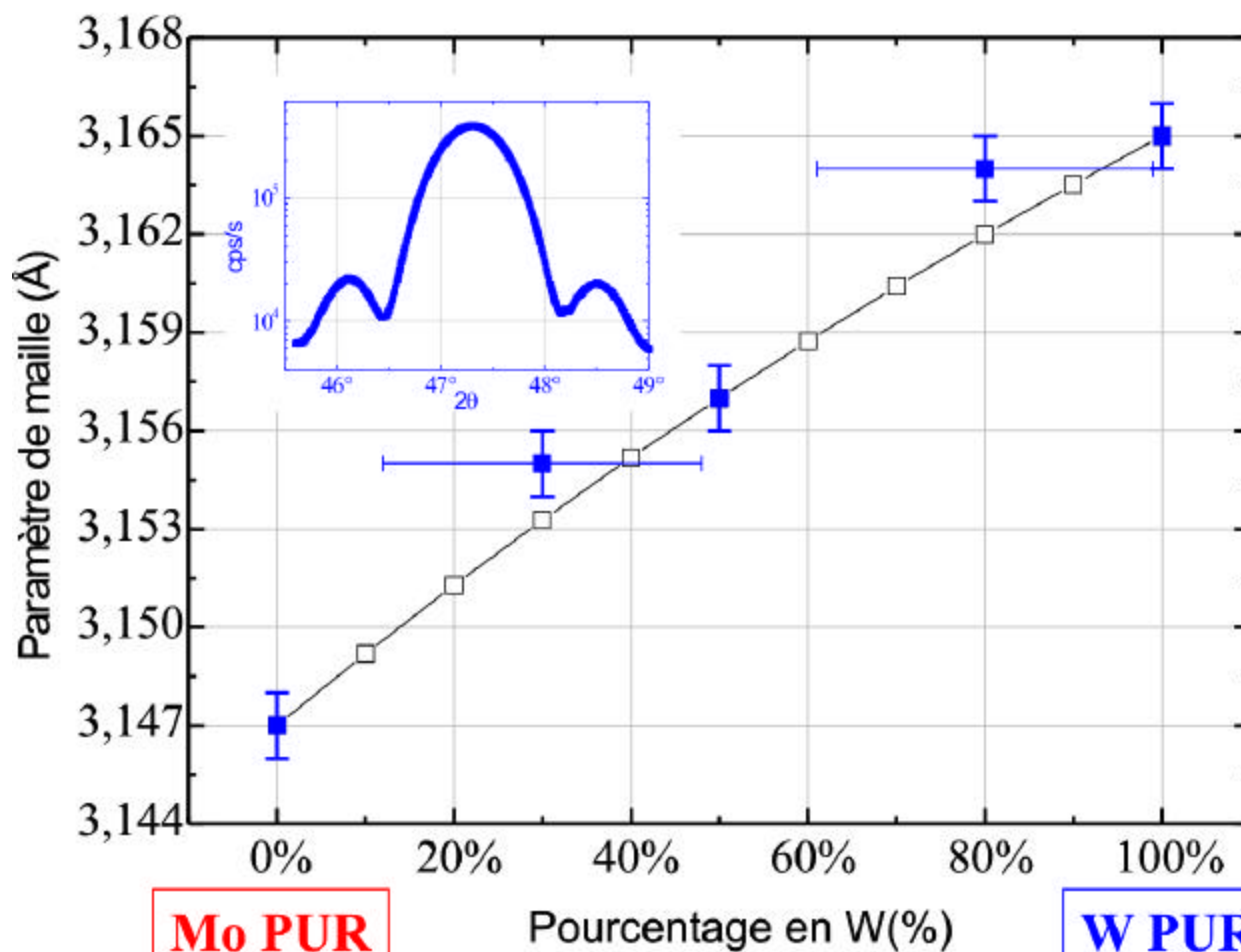
⇒ ~ Solid solution

Mo 3.147 Å



- ↪ Continuously variable buffer layer lattice parameter
- ↪ Atomically flat surface; atomic steps array

Continuous control of lattice parameter



In-plane lattice parameter from
 $a_{\text{Mo}} = 3.147 \text{ \AA}$ to
 $a_{\text{W}} = 3.165 \text{ \AA}$

Sapphire \ Mo(8nm) \ **interface** \ Fe(150°C, 450°C annealing)

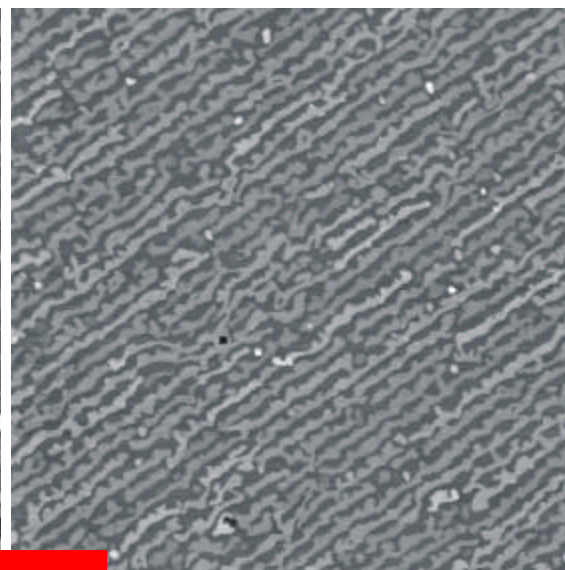
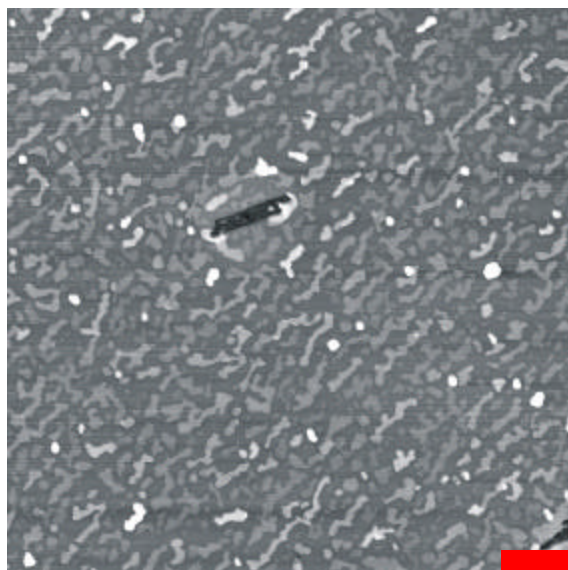
1nm

2.5nm

Average thickness



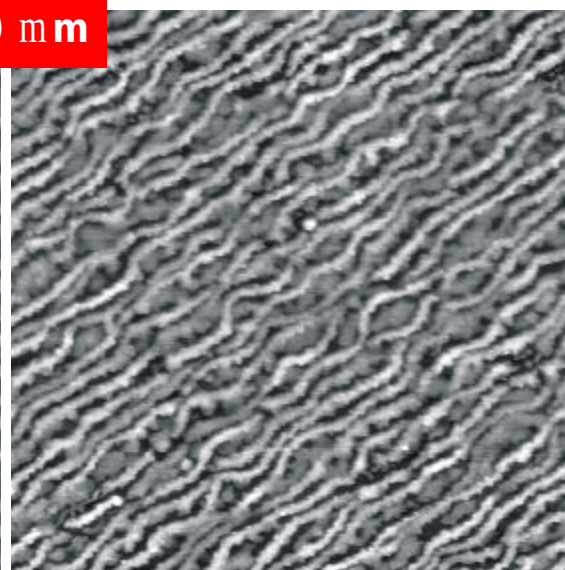
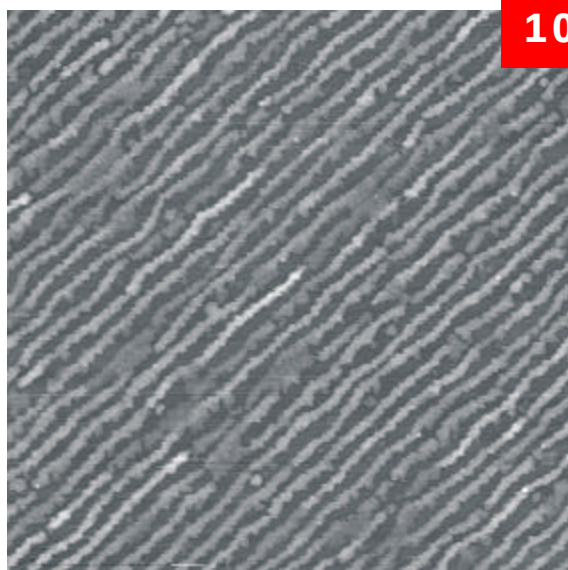
Fe
/ W (<1nm)
/ Mo



Height : 4.5nm

10 mm

Fe
/ Mo



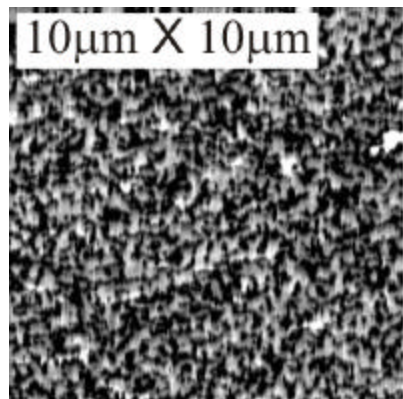
Height : bimodal
1.5 / 4nm

Chemical
interface

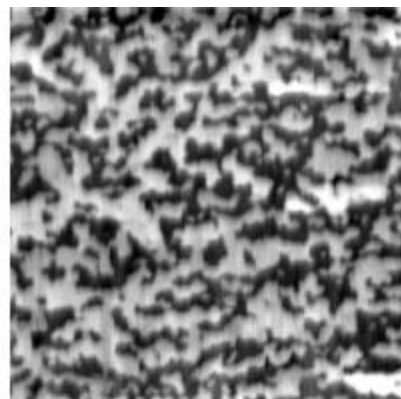
Continuous control of lattice parameter



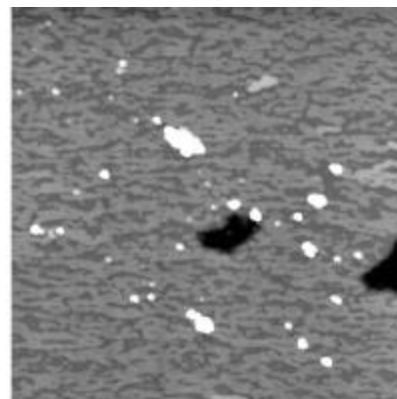
Dramatic effect on stripe growth



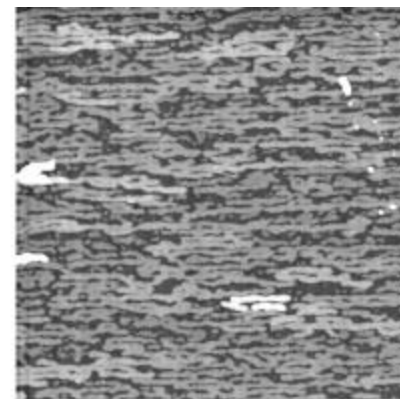
Fe/W/Mo pur



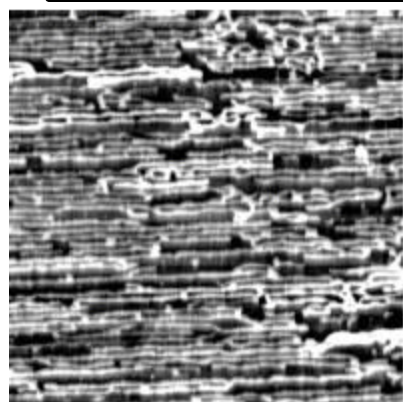
Fe/W/W_{0.2}Mo_{0.8}



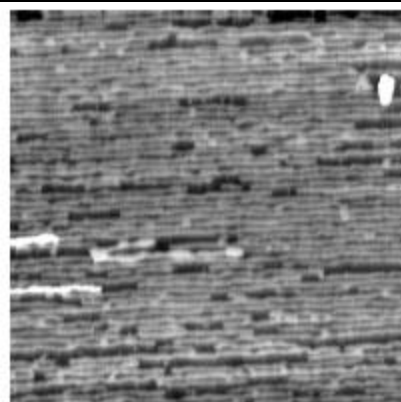
Fe/W/W_{0.4}Mo_{0.6}



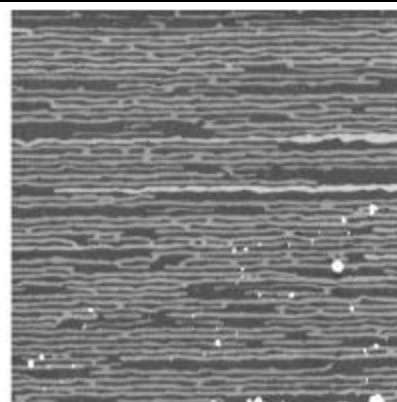
Fe/W/W_{0.5}Mo_{0.5}



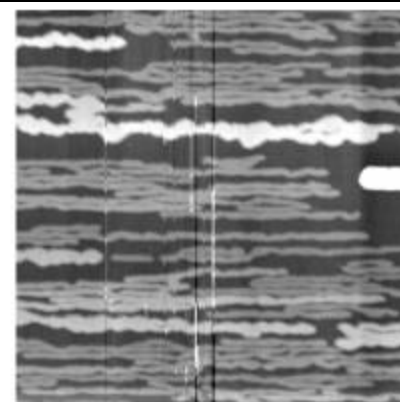
Fe/W/W_{0.6}Mo_{0.4}



Fe/W/W_{0.7}Mo_{0.3}



Fe/W/W_{0.8}Mo_{0.2}

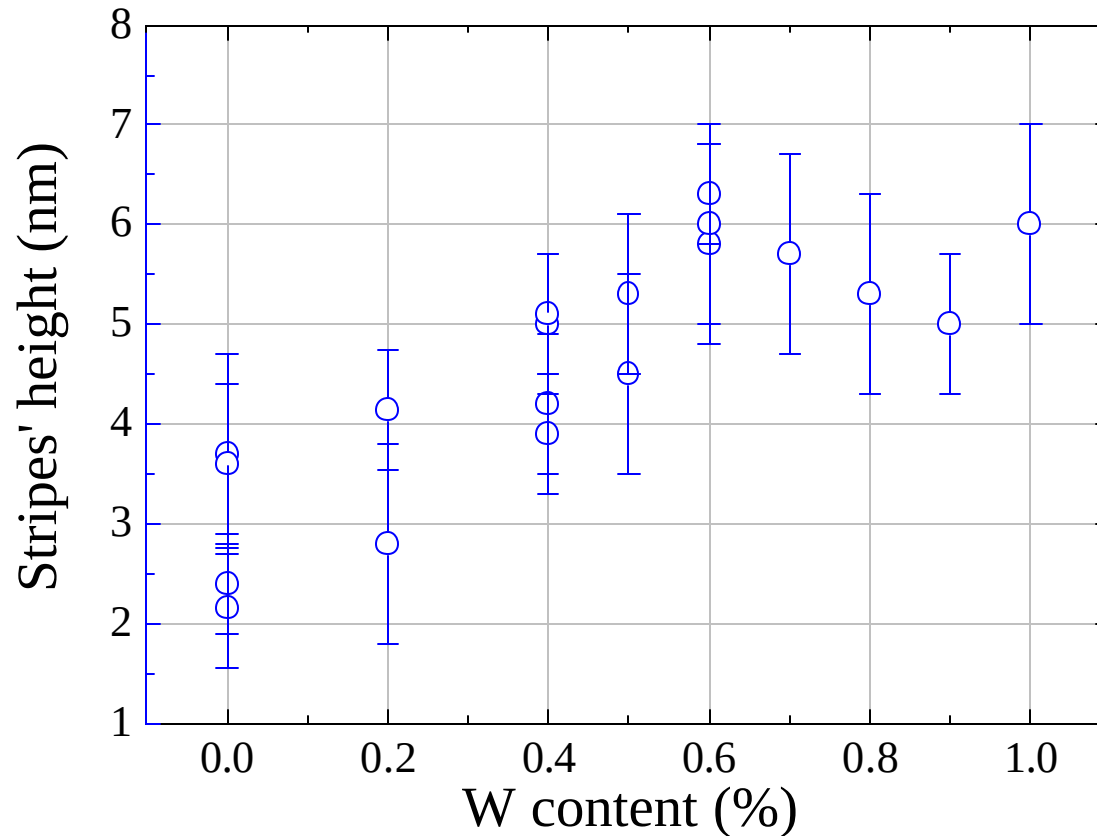


Fe/W/W pur

X

**Continuous control of lattice parameter**

Significant effect on stripe height

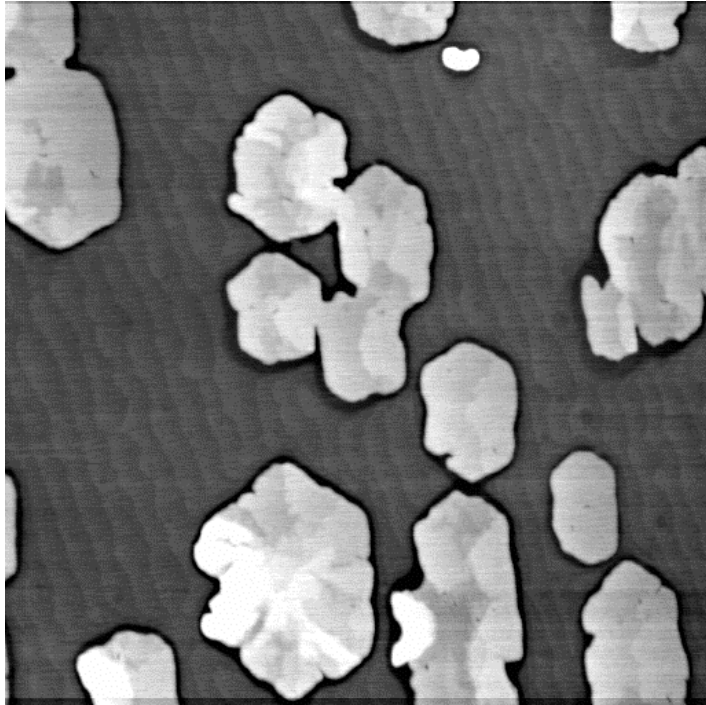


Hypothesis of commensurate/incommensurate transition needs to be confirmed

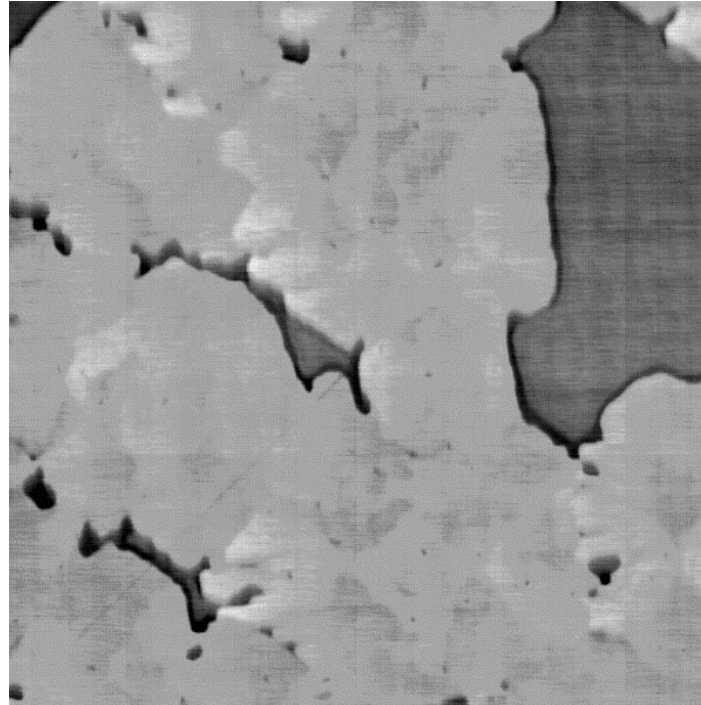
Continuous control of lattice parameter

Similar effect on patches of metastables height

$\text{Fe}(110) / \text{W}_x\text{Mo}_{1-x}$ at 800°C



3 ML Fe / Mo(110)



6 ML Fe / Mo(110)

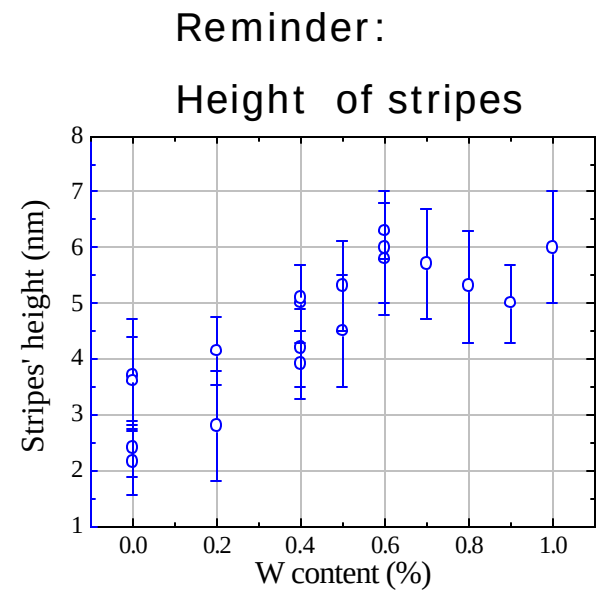
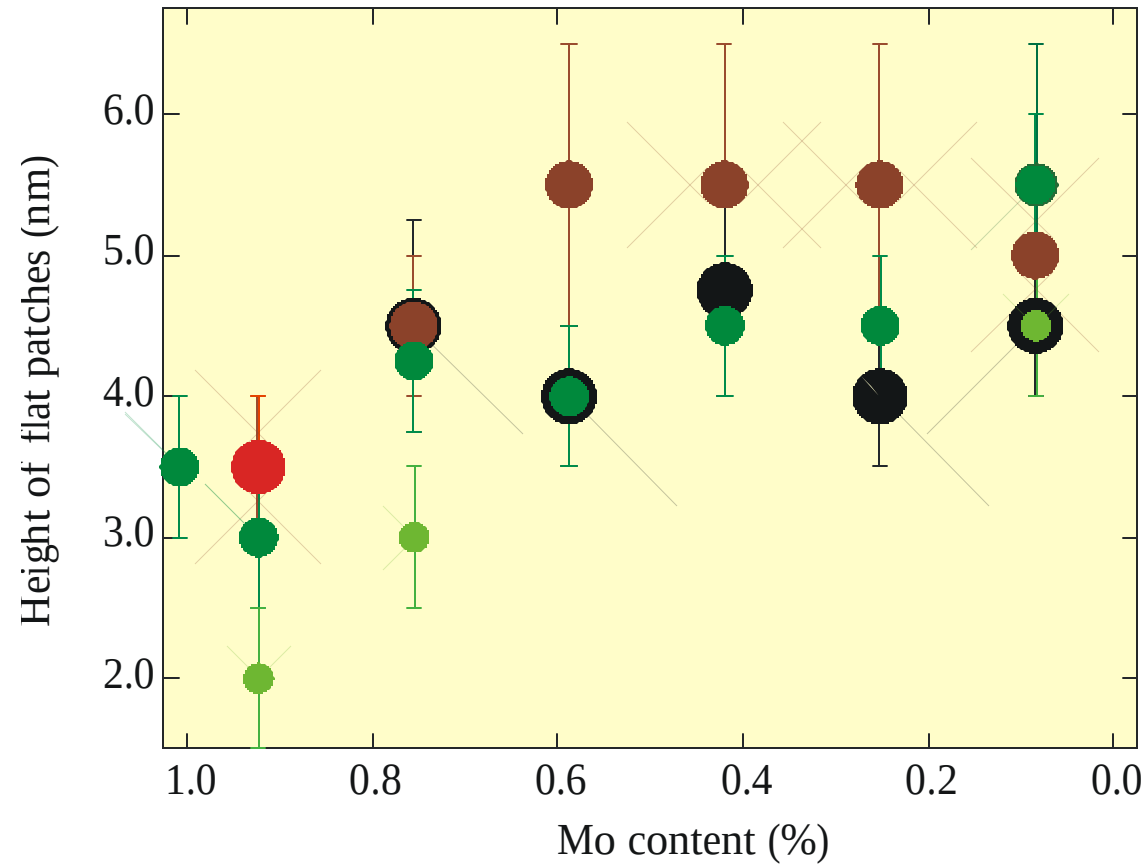
✎ Only patches of metastable height form at very high temperature
(no 3D dots)



Continuous control of lattice parameter

Similar effect on patches of metastables height

Fe(110) / W(3ML) / W_xMo_{1-x} at 800°C



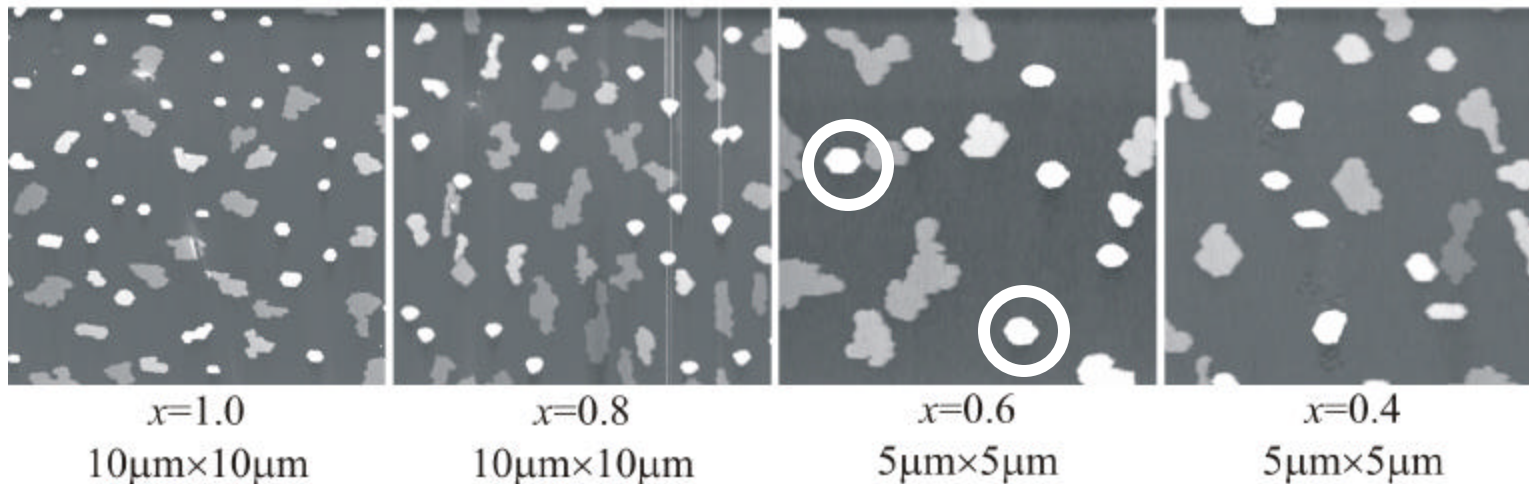
Same height for 'thick' stripes (moderate temp. Plus annealing) and flat patches (high temp. Growth)
 ↪ Thermodynamic property – Origin to be confirmed



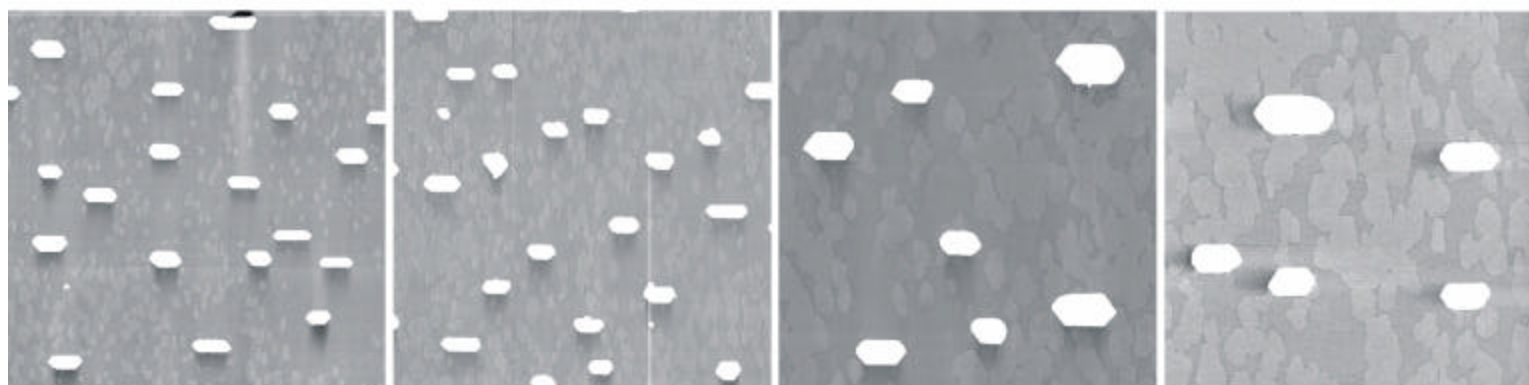


Lattice parameter : weak effect on dots

Interface W



Interface Mo → [001]



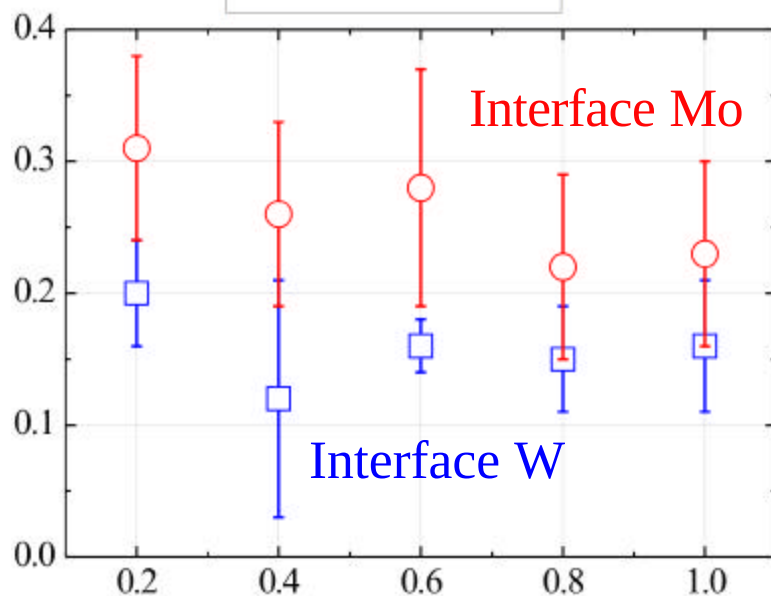
Differences: size, shape, density, aspect ratios



Weak lattice parameter change : no effect on dots

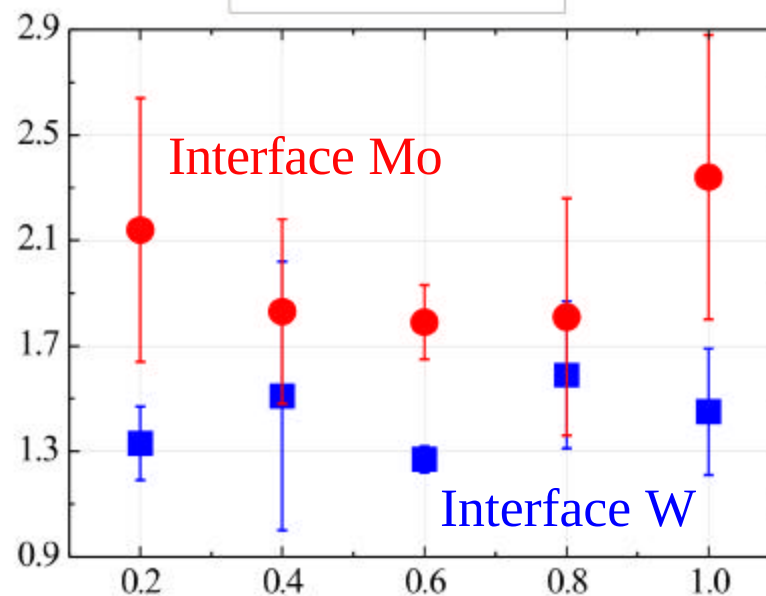
Vertical aspect ratio

$$\eta = H/W$$

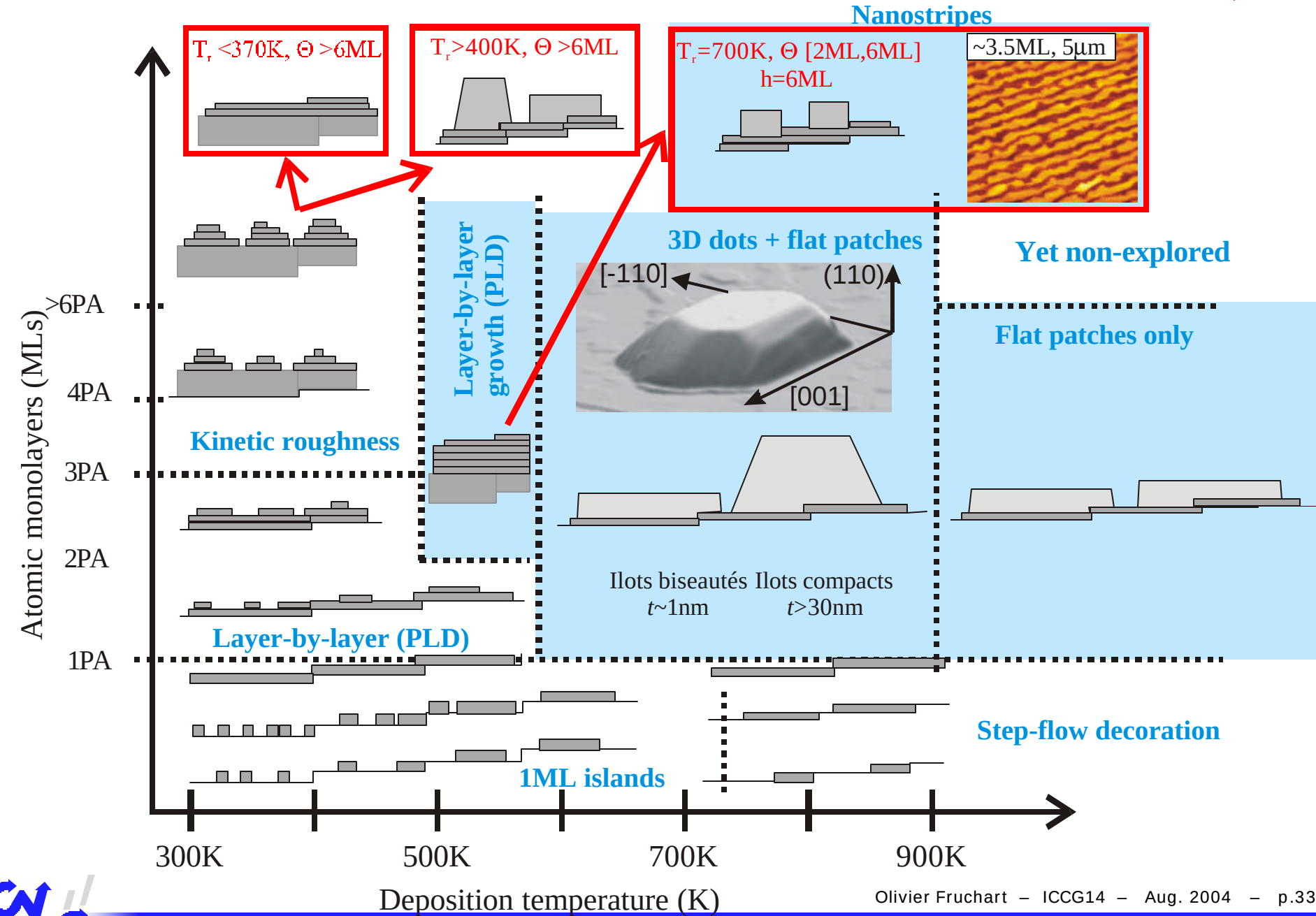


In-plane aspect ratio

$$r = L/W$$

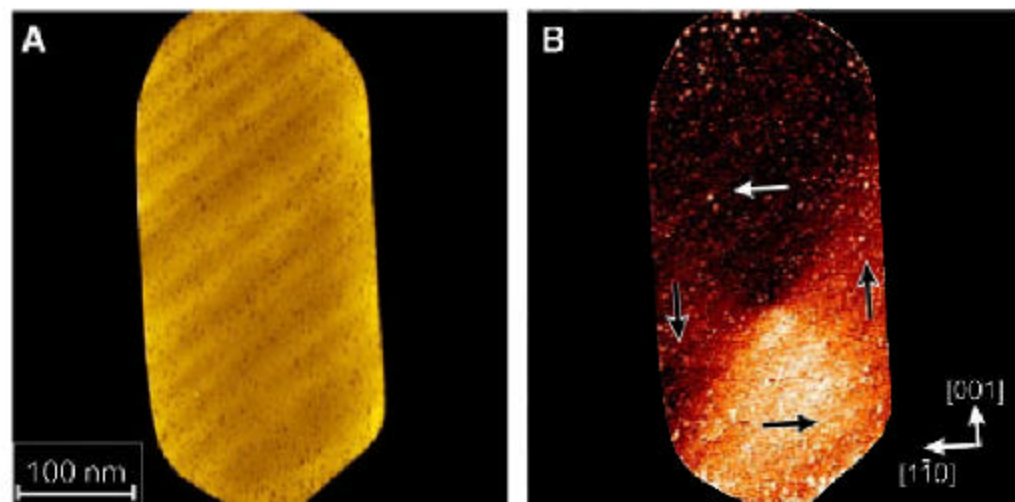


x : $W_x\text{Mo}_{1-x}$



Literature

W



A. Wachowiak et al., Science 298, 577 (2002)

Deposition at RT on W (8-10ML)

Annealing at 800 ± 100 K

Stepped substrate

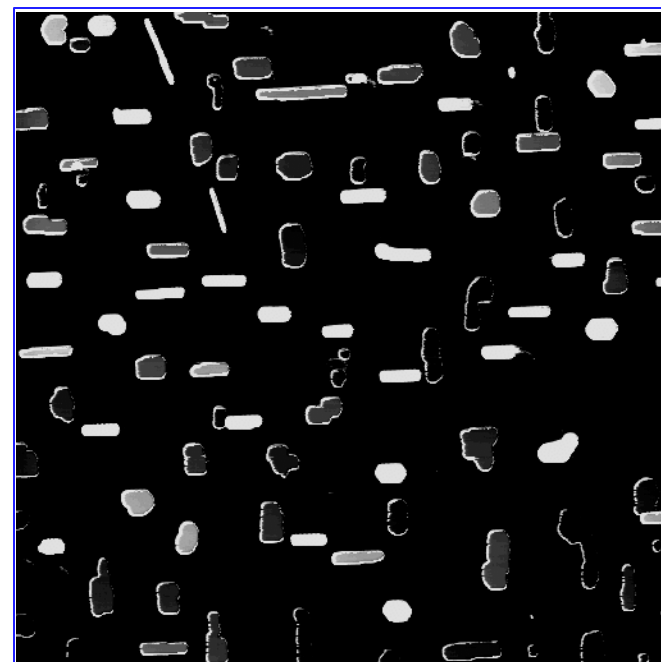
Width = 215 nm

Height = 8 nm; $r = 0.037$

Length = 471 nm; $\eta = 1.93$

Our data

W



Deposition at 775 ± 50 K

Essentially flat substrate

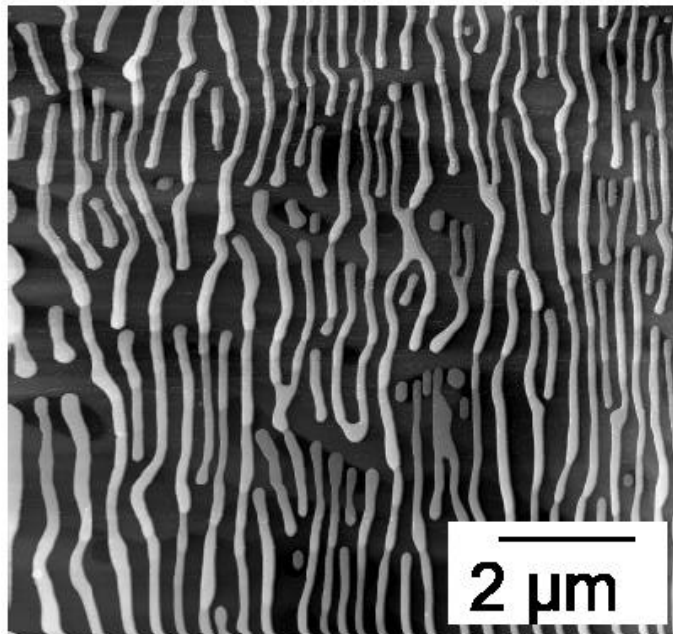
Height ratio $r = 0.07$

Length ratio $\eta = 2.3$

Consistent with 3D dots

Literature

W



D. Sander, Rep. Prog. Phys. 62, 809 (1999)

[see also Schmidt, private comm.]

Deposition at 1000K on W, or
deposition at RT and annealed 700-1000K

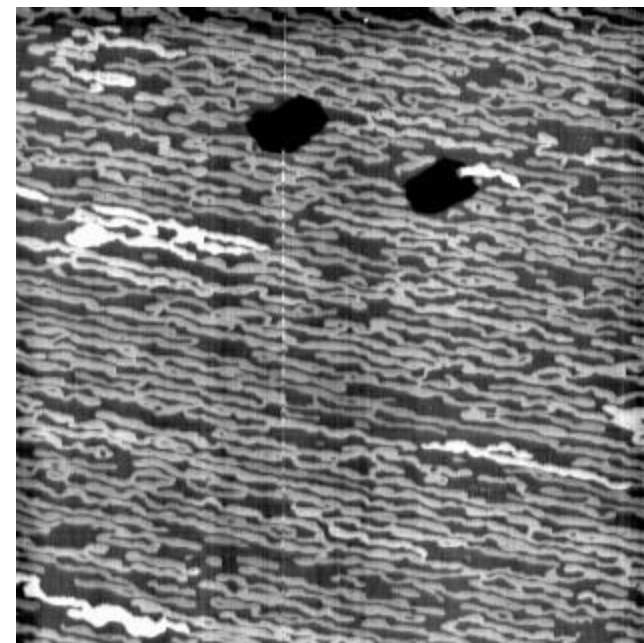
Thickness=10-20nm (private comm.)

Wires **do not follow** atomic steps

Deposition at the layer-by-layer growth
temperature is essential to keep the
information about the atomic steps

Our data

W



Deposition at 500K on W,
annealed 775±50K

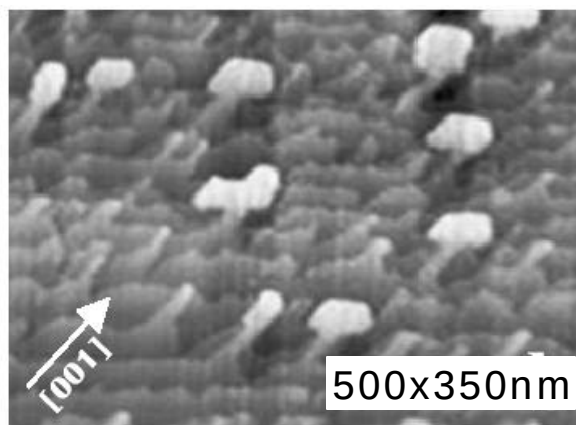
Thickness=5.5nm±0.5nm

Wires **follow** atomic steps
(1 per step)

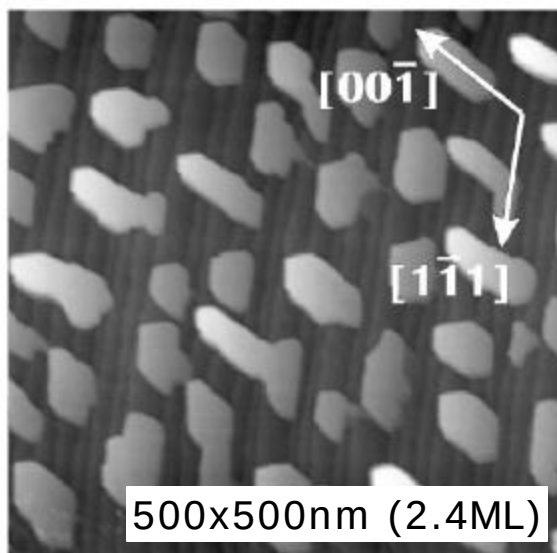


Literature

Mo



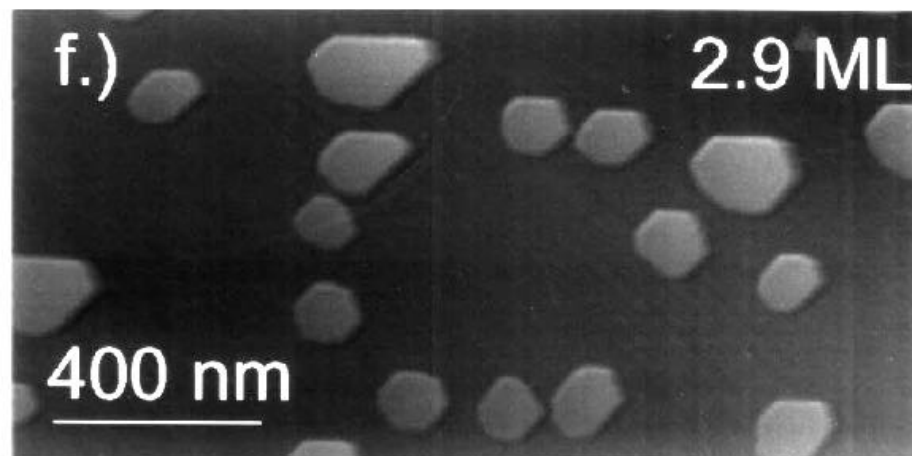
I. V. Shvets et al.,
cond-mat/0405148 (2004)



S. Murphy et al., PRB66, 195417 (2002)

Deposition at ~495K on Mo
Stepped substrate

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J. Malzbender et al., Surf. Sci. 414, 187 (1998)

[See also: Bethge et al., Koehler, Surf. Sci
331/333 (1995) 878.]

Deposition at 600K on Mo (2.9ML)

Largest thickness=10ML

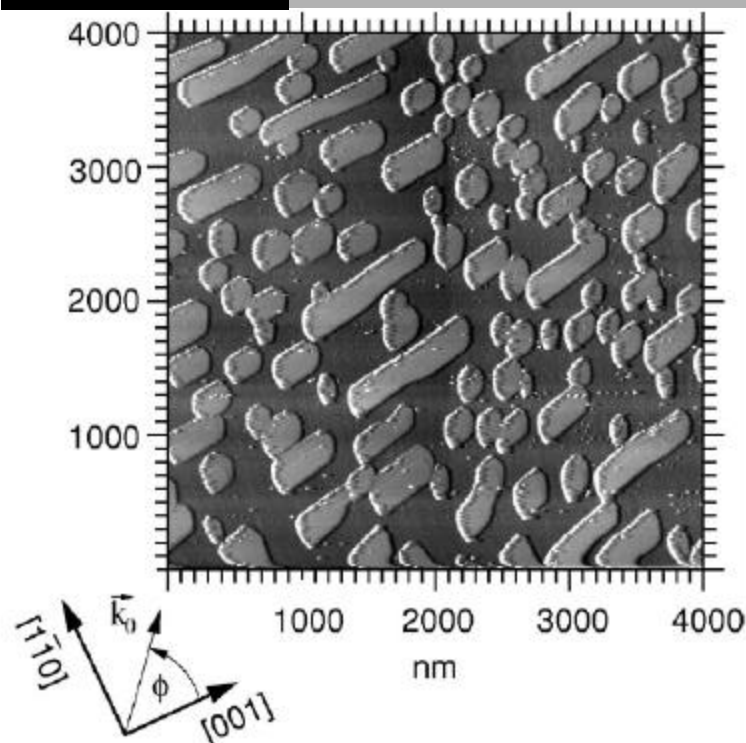
Consistent with flat dots



Onset of 3D growth not reached yet ?

Literature

W



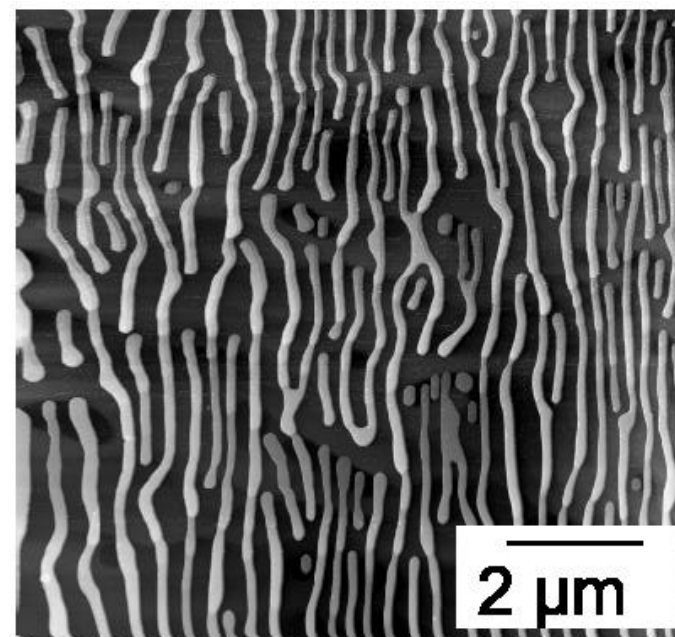
R. Röhlberger et al., PRB67, 245412 (2003)

Deposition at RT on W (5ML)
Annealing at 700K

Width=195nm

Height= 3.7 ± 0.8 nm; $r=0.019$

Length=distributed
(Cf our experiments)



D. Sander, Rep. Prog. Phys. 62, 809 (1999)

Deposition at 1000K on W, or deposition at RT and annealed 700-1000K

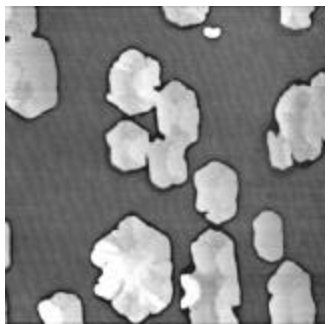
Largest thickness=10ML

In principle, same parameters used.



Influence of the step density?

Growth of Fe(110) revisited



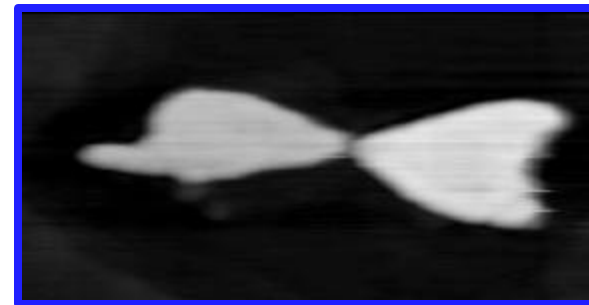
- ⇒ Evidence for bimodal island growth
- ⇒ Attempt to separate interfacial and mismatch effects



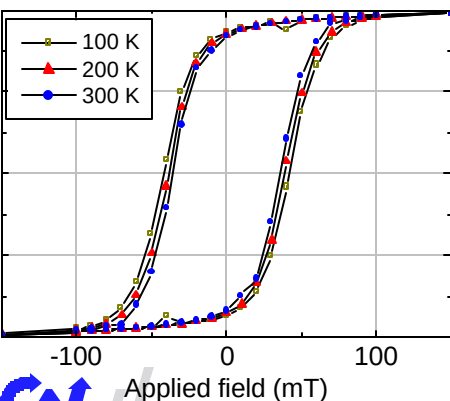
- ⇒ Tunability of the geometry of nanostructures:
 - * aspect ratios of 3D dots
 - * height of the stripes

- ⇒ New self-assembled systems
Ex: nano-tie-knots

2 μm

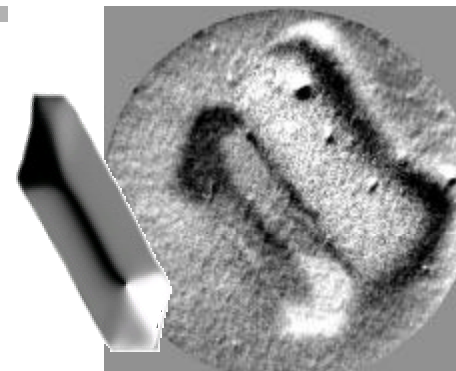


Self-assembly for magnetism



(see T02-1079, Friday)

- ⇒ Micromagnetism in 3D dots
- ⇒ Self-organized stripes magnetically functional at 300K
- ⇒ Domain wall in constriction (nano-ties)





Laboratoire Louis Néel (CNRS), Grenoble (France)

P.-O. Jubert (PhD), M. Eleoui (PhD), F. Cheynis (Master student), O. Fruchart, C. Meyer

Technical support: **V. Santonacci, Ph. David, A. Liénard, S. Biston, S. Pellé**

Growth
and magnetism

Crystallography laboratory - Grenoble (France)

L. Ortega

X-ray diffraction



Special issue on Self-organization at surfaces

Compte-Rendus Physique (C. R. Phys.), (~Jan.2005),
organized by the French Academy of Sciences

9 authors, ~100 pages (english)

Covers metals, semiconductors,
growth, characterization, physical properties

Information soon available on:

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[detailed content, direct ordering (~15€), etc.]